

Amendments to the Claims:

Following is a complete listing of the claims pending in the application, as amended:

1. (Currently amended) An image sensor comprising:
a plurality of pixels formed in a semiconductor substrate, each pixel including a light sensitive element;
a layer formed over said light sensitive elements;
a micro-lens over each of said light sensitive elements and directly atop said layer; and
a trench structure surrounding each of said micro-lenss, said trench structure formed in said layer
and extending to the interface between said layer and said micro-lens.
2. (Original) The image sensor of Claim 1 wherein said trench structure is circular.
3. (Original) The image sensor of Claim 1 wherein said trench structure has a rectangular cross-section.
4. (Original) The image sensor of Claim 1 wherein the micro-lenss are formed from polymethylmethacrylate (PMMA) or polyglycidylmethacrylate (PGMA).
5. (Currently amended) An image sensor comprising:
a plurality of pixels formed in a semiconductor substrate, each pixel including a light sensitive
element;
a micro-lens over each of said light sensitive elements; and
a trench structure surrounding each of said micro-lenss. ~~The image sensor of Claim 1~~ wherein
said trench structure has a depth on the order of 0.2 microns.

6. (Cancelled).

7. (Original) The image sensor of Claim 1 further including a color filter layer between said micro-lens and said light sensitive elements.

8. (Currently amended) A pixel of an image sensor comprising:

a light sensitive element formed in a semiconductor substrate;

a layer formed over said light sensitive element;

a micro-lens over said light sensitive element and directly atop said layer; and

a trench structure surrounding said micro-lens, said trench structure formed in said layer and extending to the interface between said layer and said micro-lens.

9. (Original) The pixel of Claim 8 wherein said trench structure is circular.

10. (Original) The pixel of Claim 8 wherein said trench structure has a rectangular cross-section.

11. (Original) The pixel of Claim 8 wherein the micro-lens is formed from polymethylmethacrylate (PMMA) or polyglycidylmethacrylate (PGMA).

12. (Currently amended) A pixel of an image sensor comprising:

a light sensitive element formed in a semiconductor substrate;

a micro-lens over said light sensitive element; and

a trench structure surrounding said micro-lens. ~~The pixel of Claim 8~~ wherein said trench structure has a depth on the order of 0.2 microns.

13. (Cancelled).

14. (Original) The pixel of Claim 8 further including a color filter layer between said micro-lens and said light sensitive elements.

15. – 19. (Cancelled)